Next generation microprobes: Detector Issues and Approaches

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Outline

- Why do we need new detectors?
- What detectors will have most impact?
- BNL development initiatives
 - Spectroscopy
 - Diffraction
 - Speckle

BNL Collaborators for silicon detector development

Zheng Li , Pavel Rehak, Wei Chen, Rolf Beuttenmuller, detector elements (Inst. Div.).

Paul O'Connor, Gianluigi De Geronimo, ASIC design (Inst. Div).

Peter Siddons, Tony Kuczewski, computer and user interface (NSLS)

Technical assistance:

John Triolo, Don Pinelli (Inst.),

Denis Poshka, Tony Lenhard, Shu Cheung, Rick Greene (NSLS)







NSLS-II

- A new 3rd-generation source at BNL
- 3GeV, 600m circumference.
- 24 TBA cells
- 5m straights
- 1.5nm-rad/0.008nm-rad
- Green-field site adjacent to NSLS
- 2012 ops.











LCLS





Generic microprobe schematic



- Includes facilities for
 - fluorescence (multi-element detector)
 - diffraction (fast readout area detector)
 - microscopy (full-field ZP microscope)







Next-generation x-ray microprobe spectroscopy detector

- Continuous-scan sample rastering
 - rapid image acquisition
 - Collaboration with CSIRO /Australian Light Source
- 400 element full-spectrum back-scatter detector array
 - <200eV resolution @ 4us</p>
 - >100kHz @ 0.5us
- Real-time quantitative multi-elemental mapping
 - Fast per-photon processing, detector response and spectral modeling









INPUT p-MOSFET

CONTINUOUS RESET

self adaptive 1pA - 100pA low noise < 3.5e⁻ rms @ 1us

highly linear < 0.2% FS

US patent 5,793,254

NIM A421, p.322

TNS 47, p.1458

NIM A480, p.713

feedback MOSFET

optimized for operating region

'HERMES' ASIC channel overview

high-order shaper



HIGH ORDER SHAPER

amplifier with passive feedback .5th order complex semigaussian .2.6x better resolution vs 2nd order .TNS 47, p.1857

BASELINE STABILIZER (BLH)

low-frequency feedback, BGR slew-rate limited follower DC and high-rate stabilization dispersion < 3mV rms stability <2mV rms @ rt×tp<0.1 .TNS 47, p.818

discriminators _____ counters

DISCRIMINATORS

five comparators 1 threshold + 2 windows four 6-bit DACs (1.6mV step) dispersion (adj) < 2.5e⁻ rms

COUNTERS

three (one per discriminator) .24-bit each

 $\approx 3 \text{ mW}$

 $\approx 5 \text{ mW}$

ASIC

High-rate multi-element detector for fluorescence measurements

398-element silicon pad array for absorption spectroscopy and/or x-ray microprobes.

Central hole for incident pump beam to allow close approach to sample. Uses 12 ASICS. Peltier cooled to -35 deg. C.









Backscattering geometry for microprobes









One quadrant with ASICS

96 pads wire-bonded to 3 ASICS.

The long bonds are rather fragile, but this approach provided least parasitic capacitance.

Each ASIC provides 32 channels of low-noise analog/digital processing.

ASIC appears to have 100% yield (no bad channels to date).









⁵⁵Fe spectrum



50µm-gap, $C_p \approx 700$ fF, $C_{i-bond} \approx 50-200$ fF, $C_{i-pad} \approx 220$ fF







Non-spectroscopic applications

Strip-shaped pixels form a 1-D position sensing detector with energy resolution (~350eV).

320 strips on 0.125mm pitch -> 40mm total length Strips 8mm long Useful for diffraction and scattering experiments.



MEDM user interface

SOFTWARE IS IMPORTANT!!!

Standard EPICS facilities allow quick GUI development, much easier than conventional GUI toolkits.

Device looks very similar to the standard EPICS scaler device, but with many more channels and additional detector control functionality.

Thresholds set via onboard DACs accessed as 'ao' records.



Powder diffraction



Total 20 sec. scan.





Charge-sharing

- Pinhole collimator measurements:
 - Green curve near edge of pixel
 - Red curve at center of pixel
- Primarily a geometrical problem
 - Absorption mask to cover gaps
 - 'Trenching' to physically separate pixels, at least on entrance side.









Next step

- Try to replace pad detectors with drift detectors.
- Work towards a system providing full spectrum per channel, instead of hardware windows
 - Same low-noise analog front-end
 - Integrate BNL Peak-detect / derandomizer module, modified for time-over-threshold mode (pileup rejection).
 - Fast ADC + FPGA + CPU to process data
 - Real-time processing







Detector array

- Mult-element array
 - 400-element drift detector array
 - Drift detector provides improved resolution at high rates
 - Central hole for incident beam
- Multi-channel ASIC
 - 32 channels
 - <200eV resolution
 - Pileup rejection circuit













Quantitative PIXE Real-time Imaging and its Application to Imaging using the Synchrotron X-ray Microprobe

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Real-time Elemental Imaging ...



Synchrotron – Nuclear Microprobe Synergy

Ryan, Etschmann, Vogt, Maser, Harland, NSLS Users Meeting, May 2004

Illustration of Dynamic Analysis using PIXE



Test of Dynamic Analysis using SXRF



CSIRO

Simple Energy Cuts



Synchrotron – Nuclear Microprobe Synergy Ryan, Etschmann,

Ryan, Etschmann, Vogt, Maser, Harland, NSLS Users Meeting, May 2004

1ms readout active-matrix area detector

- Fully pixellated detectors are complicated
- Hybrid (bump-bonded) devices add fabrication difficulties
- Monolithic devices built on high-resistivity silicon provide simplest structure
 - No bump-bonding
 - Simplest structure is active-matrix type
 - row-by-row parallel readout
 - N readout channels instead of N x N
 - Need to provide low-resistivity layer to fabricate readout structures







Pixel structure

- Low-resistivity layer is formed by deep implant.
- JFET switches are fabricated in this layer
- Charge is produced by photoionization
- Electrons collect under pixel (switch is OFF)
- Charge is read out by turning transistor ON, connecting stored charge to a buss-bar, and read out by a charge-sensitive amplifier.



Figure 6. One pixel from an Active Matrix Pixel detector array. The device is fabricated by forming a low-resistivity silicon layer suitable for JFET switching devices on top of high-resistivity silicon optimized for detector fabrication. The JFET transistors formed in this layer are used to row-sequentially switch the collected charge into column output amplifiers.







Active matrix readout

- Charge stored in diode capactance (switches off)
- Readout amplifier/ADC on each column
- Switches turned on sequentially row-by-row
- Charge read out and digitized
- 1us per row => 1ms for 1000 rows.
 - 8-channel
 40MHz/channel ADC
 chip exists
 - 32 chips, each ADC multiplexed among 4 columns
 - 2Gb/s data rate









View of a completed wafer









Prototype device

- Part of an 8 x 8 pixel test device
- 180 um square pixels









Alternative small-pixel structure

- Small pixels are difficult with transistor switch
- Charge can be stored in potential well and released in a controlled way, similar to drift detectors.
- This 'charge pump' technology is ideal for speckle applications.

Top view of a pixel with a charge pump single transfer









Charge pumping (no transistor) Þ_{ixel Without sig. el.} (_{confined}) 25 Þixel without sig. el. (transfer) 10 Steam - Sec 20 Strate Curry -Constant and the second second







Readout system

- Row-by-row readout, 1us/row
- 32 Fast (>20MHz) 8channel ADC's multiplexed e.g. x4 = 1024
- 2Gb/s
- Data streamed through FPGA to fast memory and terabyte disk store.









SRC MAPstation[™]

SRC-6 uses standard external network connections



MAP[®] Implementation



- Direct Execution Logic (DEL) made up of one or more User Logic devices
- Control circuits allow explicit control of memory prefetch and data access
- Multiple banks of On-Board Memory maximizes local memory bandwidth
- GPIO ports allow direct MAP to MAP chain connections or direct data input
 - Multiple DMA engines support
 - Distributed SRAM in User Logic
 264 KB @ 844 GB/s
 - Block SRAM in User Logic
 - 648 KB @ 260 GB/s
 - On-Board SRAM
 - 28 MB @ 9.6 GB/s
 - Microprocessor Memory
 - 8 GB @ 1400 MB/s



Embedded Compact MAP[®] System



Compilation and Linking



Summary

- A path to satisfying the needs of current and nextgeneration microprobes exists
 - Spectroscopy
 - Diffraction
 - Speckle
- The demand for higher-performance instruments is clear
 - Higher rate capability
 - Better throughput
 - better utilization of photons
 - Better (and real-time) analysis
- It will take all of us to push hard if anything is to happen.